Product data sheet

1. General description

N-channel enhancement mode Field-Effect Transistor (FET) in a leadless ultra small DFN1006B-3 (SOT883B) Surface-Mounted Device (SMD) plastic package using Trench MOSFET technology.

2. Features and benefits

- Logic-level compatible
- Very fast switching
- Trench MOSFET technology
- ElectroStatic Discharge (ESD) protection > 2kV HBM

3. Applications

- Relay driver
- High-speed line driver
- Low-side loadswitch
- Switching circuits

4. Quick reference data

Table 1. Quick reference data

Symbol	Parameter	Conditions		Min	Тур	Max	Unit	
V _{DS}	drain-source voltage	T _j = 25 °C		-	-	60	V	
V _{GS}	gate-source voltage			-20	-	20	V	
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	-	350	mA	
Static characte	Static characteristics							
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 200 mA; T_j = 25 °C		-	2.2	2.8	Ω	

^[1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².





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5. Pinning information

Table 2. Pinning information

Pin	Symbol	Description	Simplified outline	Graphic symbol
1	G	gate	1 🔲	D I
2	S	source	2 3	
3	D	drain	Transparent top view DFN1006B-3 (SOT883B)	G S 017aaa255

6. Ordering information

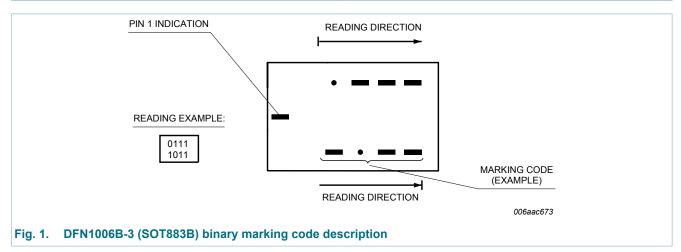
Table 3. Ordering information

Type number	Package				
	Name	Description	Version		
NX7002BKMB	DFN1006B-3	DFN1006B-3: leadless ultra small plastic package; 3 solder lands; body 1.0 x 0.6 x 0.37 mm	SOT883B		

7. Marking

Table 4. Marking codes

Type number	Marking code
NX7002BKMB	0101 0111



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8. Limiting values

Table 5. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions		Min	Max	Unit
V _{DS}	drain-source voltage	T _j = 25 °C		-	60	V
V_{GS}	gate-source voltage			-20	20	V
I _D	drain current	V _{GS} = 10 V; T _{amb} = 25 °C	[1]	-	350	mA
		V _{GS} = 10 V; T _{amb} = 100 °C	[1]	-	200	mA
I _{DM}	peak drain current	T_{amb} = 25 °C; single pulse; $t_p \le 10 \mu s$		-	0.9	Α
P _{tot}	total power dissipation	T _{amb} = 25 °C	[2]	-	350	mW
			[1]	-	680	mW
		T _{sp} = 25 °C		-	3100	mW
Tj	junction temperature			-55	150	°C
T _{amb}	ambient temperature			-55	150	°C
T _{stg}	storage temperature			-65	150	°C
Source-dra	in diode				'	,
Is	source current	T _{amb} = 25 °C	[1]	-	200	mA

- [1] Device mounted on an FR4 Printed-Circuit Board (PCB), single-sided copper, tin-plated, mounting pad for drain 1 cm².
- [2] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

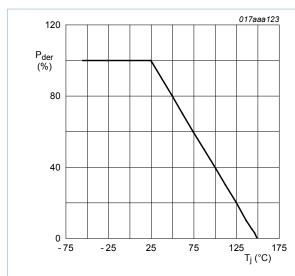


Fig. 2. Normalized total power dissipation as a function of junction temperature

$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100 \%$$

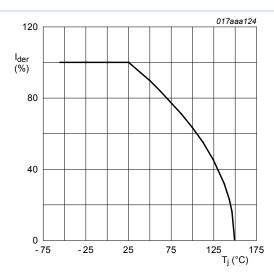


Fig. 3. Normalized continuous drain current as a function of junction temperature

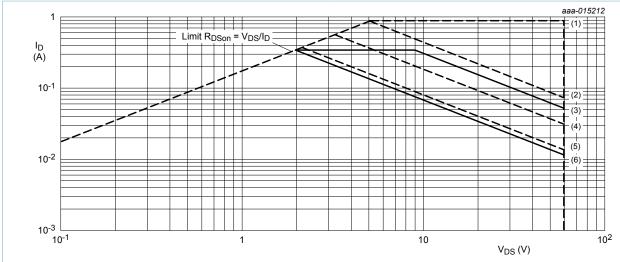
$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100 \%$$

NX7002BKMB

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I_{DM} = single pulse

(1)
$$t_p = 10 \mu s$$

(2)
$$t_p = 1 \text{ ms}$$

(3) DC;
$$T_{sp} = 25 \,^{\circ}\text{C}$$

(4)
$$t_p = 10 \text{ ms}$$

$$(5) t_p = 100 \text{ ms}$$

(6) DC; T_{amb} = 25 °C; drain mounting pad 1 cm²

Fig. 4. Safe operating area; junction to ambient; continuous and peak drain currents as a function of drainsource voltage

9. Thermal characteristics

Table 6. Thermal characteristics

Symbol	Parameter	Conditions		Min	Тур	Max	Unit
R _{th(j-a)}	thermal resistance from junction to ambient	in free air	[1]	-	314	360	K/W
			[2]	-	159	180	K/W
R _{th(j-sp)}	thermal resistance from junction to solder point			-	35	40	K/W

^[1] Device mounted on an FR4 PCB, single-sided copper, tin-plated and standard footprint.

^[2] Device mounted on an FR4 PCB, single-sided copper, tin-plated, mounting pad for drain 1 cm².

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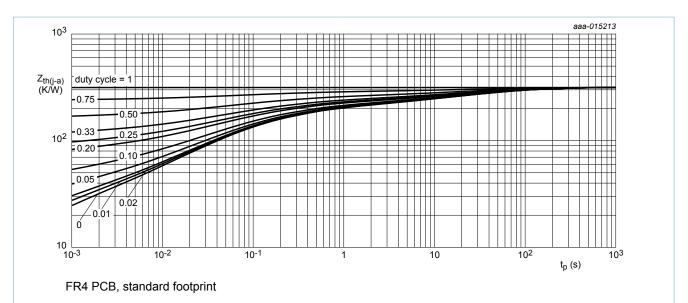


Fig. 5. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

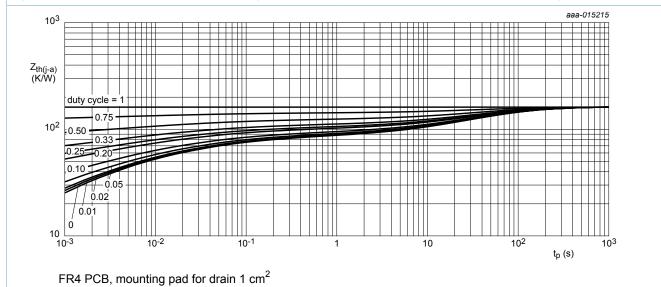


Fig. 6. Transient thermal impedance from junction to ambient as a function of pulse duration; typical values

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10. Characteristics

Table 7 Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static char	acteristics			'		
$V_{(BR)DSS}$	drain-source breakdown voltage	I_D = 250 μ A; V_{GS} = 0 V; T_j = 25 °C	60	-	-	V
V_{GSth}	gate-source threshold voltage	$I_D = 250 \mu A; V_{DS} = V_{GS}; T_j = 25 \text{ °C}$	1.1	1.6	2.1	V
I _{DSS}	drain leakage current	V _{DS} = 60 V; V _{GS} = 0 V; T _j = 25 °C	-	-	1	μΑ
I _{GSS}	gate leakage current	V _{GS} = 20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	10	μA
		V _{GS} = -20 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-10	μΑ
		V _{GS} = 10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	1	μΑ
		V _{GS} = -10 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-1	μΑ
		V _{GS} = 5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	0.3	μΑ
		V _{GS} = -5 V; V _{DS} = 0 V; T _j = 25 °C	-	-	-0.3	μΑ
R _{DSon}	drain-source on-state resistance	V_{GS} = 10 V; I_D = 200 mA; T_j = 25 °C	-	2.2	2.8	Ω
resistance		V _{GS} = 10 V; I _D = 100 mA; T _j = 150 °C	-	4.5	5.7	Ω
		V _{GS} = 5 V; I _D = 200 mA; T _j = 25 °C	-	2.5	3.2	Ω
9 _{fs}	forward transconductance	V_{DS} = 10 V; I_D = 200 mA; T_j = 25 °C	-	600	-	mS
R_G	internal gate resistance (AC)	f = 2.5 MHz	-	2.5	-	Ω
Dynamic cl	naracteristics			'		
Q _{G(tot)}	total gate charge	V_{DS} = 30 V; I_{D} = 200 mA; V_{GS} = 10 V;	-	1	-	nC
Q _{GS}	gate-source charge	T _j = 25 °C	-	0.12	-	nC
Q_{GD}	gate-drain charge		-	0.18	-	nC
C _{iss}	input capacitance	V _{DS} = 10 V; f = 1 MHz; V _{GS} = 0 V;	-	23.6	-	pF
C _{oss}	output capacitance	T _j = 25 °C	-	4.6	-	pF
C _{rss}	reverse transfer capacitance		-	3	-	pF
t _{d(on)}	turn-on delay time	V _{DS} = 50 V; I _D = 200 mA; V _{GS} = 10 V;	-	4.7	-	ns
t _r	rise time	$R_{G(ext)} = 6 \Omega; T_j = 25 °C$	-	4.3	-	ns
t _{d(off)}	turn-off delay time		-	6.9	-	ns
t _f	fall time		-	2.9	-	ns
Source-dra	in diode		ı	1		
V _{SD}	source-drain voltage	$I_S = 200 \text{ mA}; V_{GS} = 0 \text{ V}; T_j = 25 ^{\circ}\text{C}$	-	0.87	1.2	V

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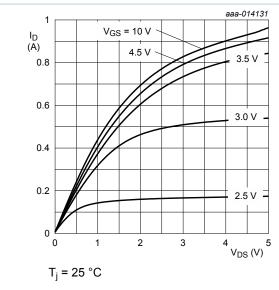


Fig. 7. Output characteristics: drain current as a function of drain-source voltage; typical values

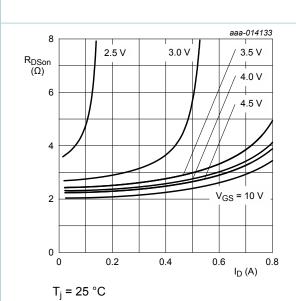
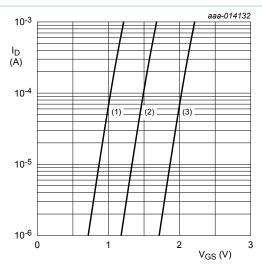


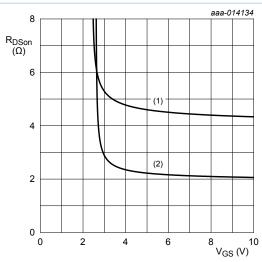
Fig. 9. Drain-source on-state resistance as a function of drain current; typical values



 $T_i = 25 \,^{\circ}C; V_{DS} = 5 \,^{\circ}V$

- (1) minimum values
- (2) typical values
- (3) maximum values

Fig. 8. Sub-threshold drain current as a function of gate-source voltage



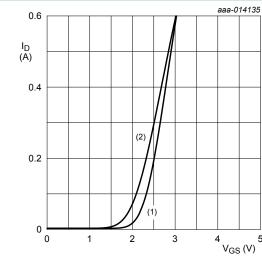
 $I_D = 0.2 A$

(1) $T_i = 150 \, ^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig. 10. Drain-source on-state resistance as a function of gate-source voltage; typical values

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 $V_{DS} > I_{D} \times R_{DSon}$

(1) $T_j = 25 \, ^{\circ}C$

(2) $T_j = 150 \, ^{\circ}C$

Fig. 11. Transfer characteristics: drain current as a function of gate-source voltage; typical values

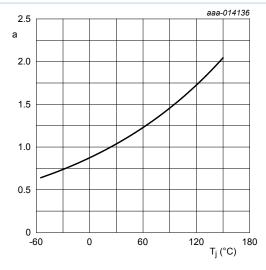
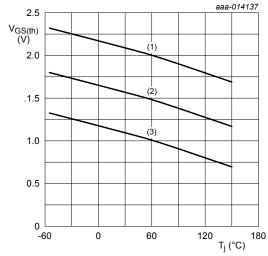


Fig. 12. Normalized drain-source on-state resistance as a function of junction temperature; typical values

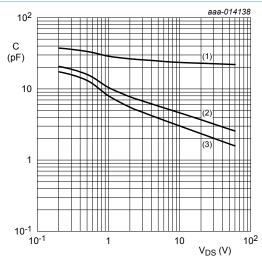
$$a = \frac{R_{DSon}}{R_{DSon(25^{\circ}C)}}$$



 $I_D = 0.25 \text{ mA}; V_{DS} = V_{GS}$

- (1) maximum values
- (2) typical values
- (3) minimum values

Fig. 13. Gate-source threshold voltage as a function of junction temperature



f = 1 MHz; V_{GS} = 0 V

- (1) C_{iss}
- (2) C_{oss}
- (3) C_{rss}

Fig. 14. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values

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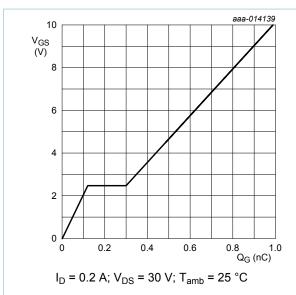


Fig. 15. Gate-source voltage as a function of gate charge; typical values

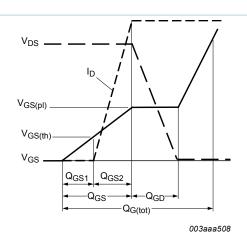
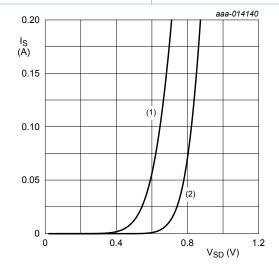


Fig. 16. MOSFET transistor: Gate charge waveform definitions



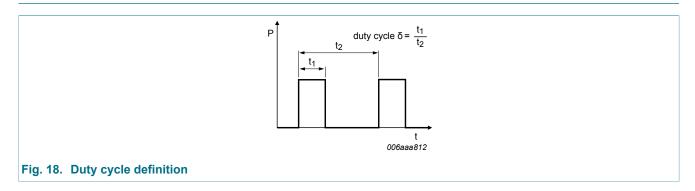
 $V_{GS} = 0 V$ (1) $T_j = 150 \,^{\circ}C$

(2) $T_i = 25 \, ^{\circ}C$

Fig. 17. Source current as a function of source-drain voltage; typical values

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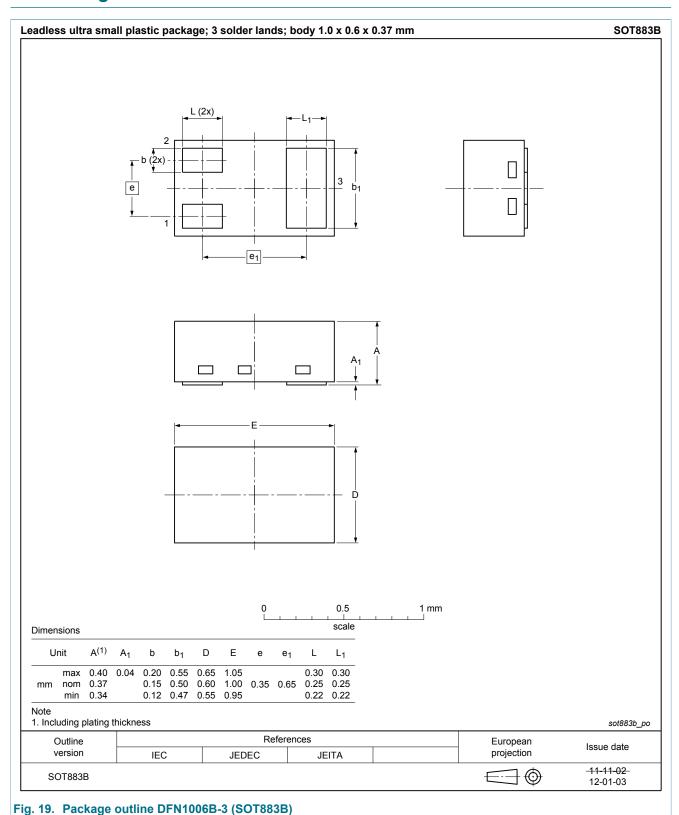
11. Test information



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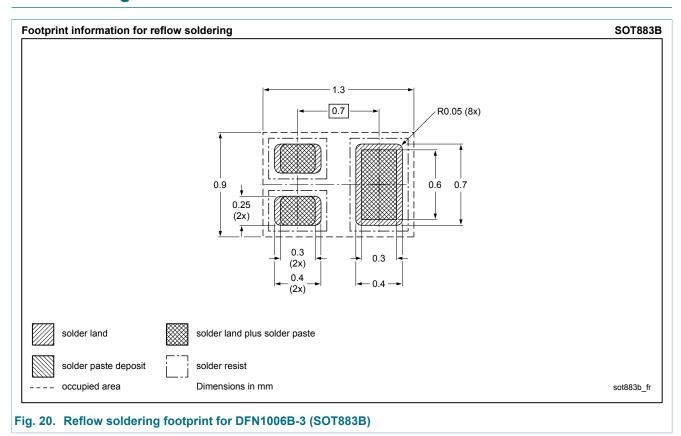
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12. Package outline



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13. Soldering



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14. Revision history

Table 8. Revision history

Data sheet ID	Release date	Data sheet status	Change notice	Supersedes
NX7002BKMB v.2	20141203	Product data sheet	-	NX7002BKMB v.1
Modification:	Figure 3 updated			
NX7002BKMB v.1	20141001	Product data sheet	-	-

60 V, N-channel Trench MOSFET

15. Legal information

15.1 Data sheet status

Document status [1][2]	Product status [3]	Definition
Objective [short] data sheet	Development	This document contains data from the objective specification for product development.
Preliminary [short] data sheet	Qualification	This document contains data from the preliminary specification.
Product [short] data sheet	Production	This document contains the product specification.

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